

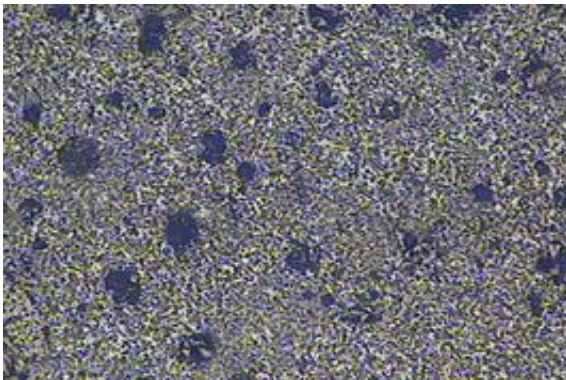
## About Sintered Silicon Carbide+Graphite (SSiC+C)



The Sintered Silicon Carbide+Graphite material is formed by sintering an atomic crystal composed of a strong covalent bond of Si-C and a flexible carbon in a vacuum sintering furnace at 2100 °C. The Sintered Silicon Carbide+Graphite have the properties of the original sintered silicon carbide material, such as strong corrosion resistance, wear resistance, high electrical conductivity and high temperature stability, and the

addition of graphite increases the self-lubricity and reduces the friction coefficient, and is more suitable for Under the conditions of instantaneous dry friction and long-term semi-dry friction, it is applied in the fields of new energy, chemical industry, shipbuilding and scientific research and defense military technology.

### Characteristics



The crystal phase diagram of the Sintered Silicon Carbide+Graphite material is chemically treated on the smooth and smooth fracture surface of the material. The crystal and graphite (content 5-10%) under the 200X optical microscope are evenly distributed, uniform in size and dense.

### Sintered Silicon Carbide+Graphite Technical Data

Item	Unit	SSiC+C
Volume Density	g/cm <sup>3</sup>	2.95~3.05
Rockwell hardness	HRA	≥90
Indicated Porosity	%	<0.2
Compressive Strength	Mpa	≥1500
Flexural Strength	Mpa	≥250
Elastic Modulus	GPa	300
Thermal Conductivity	W/m <sup>2</sup> K	120
Maximum Temperature	°C	1500
Coefficient Of Heat Expansion	10 <sup>-6</sup> /°C	3.0
Graphite	%	5~10